## Erratum Oxidation kinetics of hot-pressed silicon carbide

S. C. SINGHAL Metallurgy and Metals Processing, Westinghouse Research Laboratories, Pittsburgh, Pennsylvania, USA

J. Mater. Sci. 11 (1976) 1246-1253.

Figure 5, page 1250, was incorrectly printed. The correct version is given below.

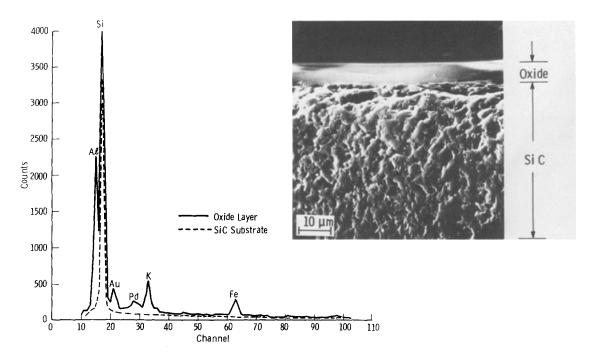


Figure 5 Scanning electron micrograph of the transverse section of a SiC specimen oxidized at 1370° C for 1203 h with energy dispersive X-ray analysis in the oxide layer and in the SiC substrate.